

CR6PM-12

Thyristor

Medium Power Use

REJ03G0358-0100

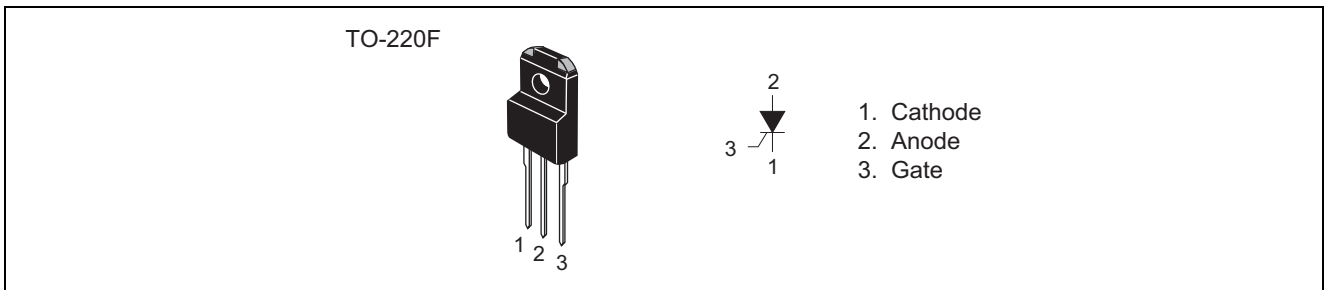
Rev.1.00

Aug.20.2004

Features

- $I_{T(AV)}$: 6 A
- V_{DRM} : 600 V
- I_{GT} : 10 mA
- V_{ISO} : 1500V
- Insulated Type
- Planar Passivation Type
- UL Recognized : Yellow Card No. E223904
File No. E80271

Outline



Applications

Switching mode power supply, regulator for autcycle, motor control, heater control, and other general purpose control applications

Maximum Ratings

Parameter	Symbol	Voltage class	Unit
		12	
Repetitive peak reverse voltage	V_{RRM}	600	V
Non-repetitive peak reverse voltage	V_{RSM}	720	V
DC reverse voltage	$V_{R(DC)}$	480	V
Repetitive peak off-state voltage	V_{DRM}	600	V
DC off-state voltage	$V_{D(DC)}$	480	V

Parameter	Symbol	Ratings	Unit	Conditions
RMS on-state current	$I_{T(RMS)}$	9.4	A	
Average on-state current	$I_{T(AV)}$	6	A	Commercial frequency, sine half wave 180° conduction, $T_c = 85^\circ\text{C}$
Surge on-state current	I_{TSM}	90	A	60Hz sine half wave 1 full cycle, peak value, non-repetitive
I^2t for fusing	I^2t	34	A^2s	Value corresponding to 1 cycle of half wave 60Hz, surge on-state current
Peak gate power dissipation	P_{GM}	5	W	
Average gate power dissipation	$P_{G(AV)}$	0.5	W	
Peak gate forward voltage	V_{FGM}	6	V	
Peak gate reverse voltage	V_{RGM}	10	V	
Peak gate forward current	I_{FGM}	2	A	
Junction temperature	T_j	- 40 to +125	$^\circ\text{C}$	
Storage temperature	T_{stg}	- 40 to +125	$^\circ\text{C}$	
Mass	—	2.0	g	Typical value
Isolation voltage	Viso	1500	V	$T_a = 25^\circ\text{C}$, AC 1 minute, each terminal to case

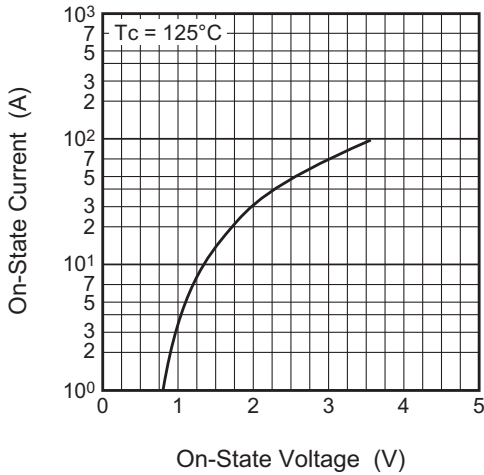
Electrical Characteristics

Parameter	Symbol	Rated value			Unit	Test conditions
		Min.	Typ.	Max.		
Repetitive peak reverse current	I_{RRM}	—	—	2.0	mA	$T_j = 125^\circ\text{C}$, V_{RRM} applied
Repetitive peak off-state current	I_{DRM}	—	—	2.0	mA	$T_j = 125^\circ\text{C}$, V_{DRM} applied
On-state voltage	V_{TM}	—	—	1.7	V	$T_c = 25^\circ\text{C}$, $I_{TM} = 20\text{ A}$, instantaneous value
Gate trigger voltage	V_{GT}	—	—	1.0	V	$T_j = 25^\circ\text{C}$, $V_D = 6\text{ V}$, $I_T = 1\text{ A}$
Gate non-trigger voltage	V_{GD}	0.2	—	—	V	$T_j = 125^\circ\text{C}$, $V_D = 1/2 V_{DRM}$
Gate trigger current	I_{GT}	—	—	10	mA	$T_j = 25^\circ\text{C}$, $V_D = 6\text{ V}$, $I_T = 1\text{ A}$
Holding current	I_H	—	15	—	mA	$T_j = 25^\circ\text{C}$, $V_D = 12\text{ V}$
Thermal resistance	$R_{th(j-c)}$	—	—	4.0	$^\circ\text{C/W}$	Junction to case ^{Note1}

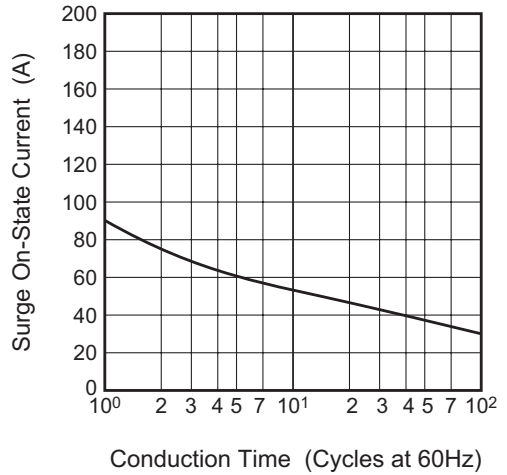
Notes: 1. The contact thermal resistance $R_{th(c-f)}$ in case of greasing is 0.5°C/W .

Performance Curves

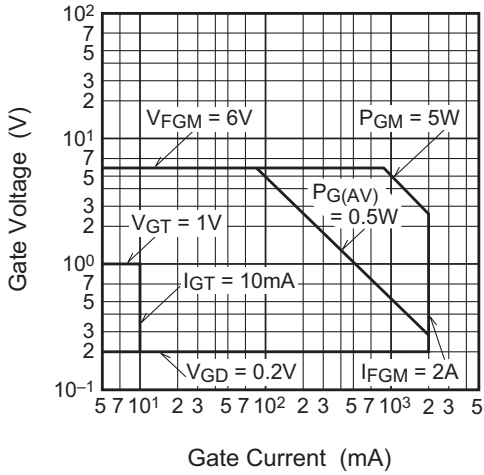
Maximum On-State Characteristics



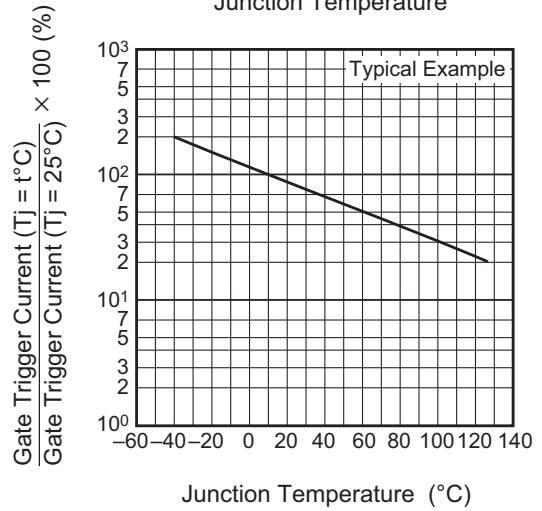
Rated Surge On-State Current



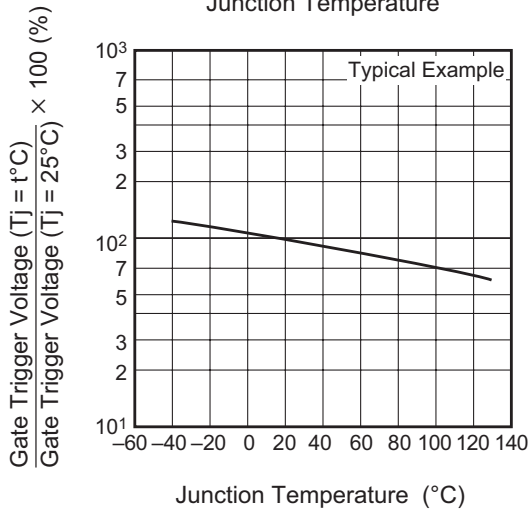
Gate Characteristics



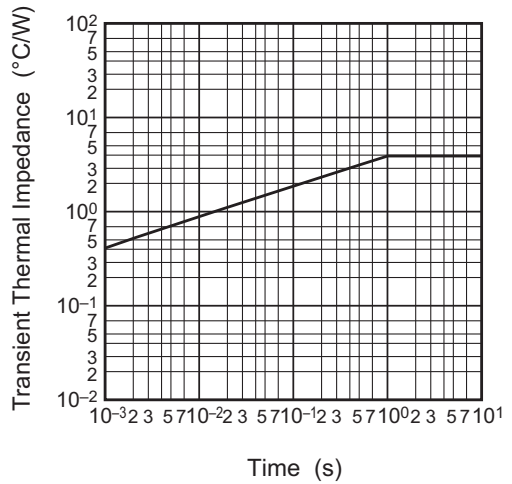
Gate Trigger Current vs. Junction Temperature

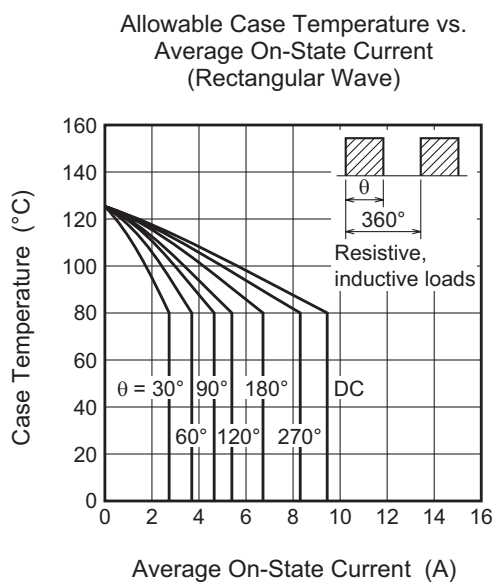
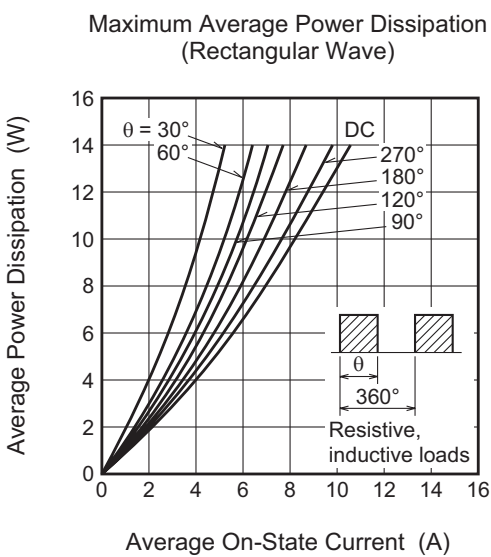
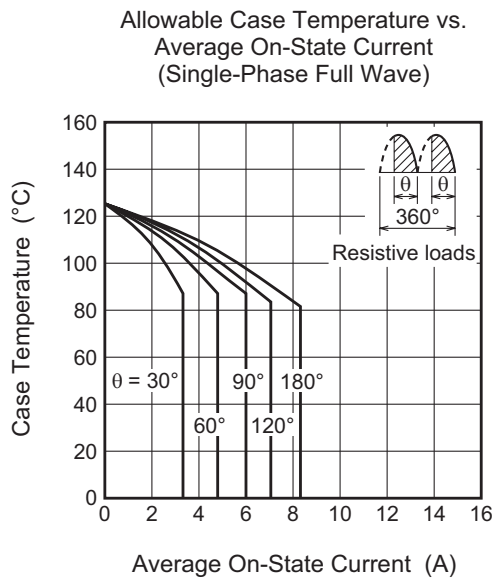
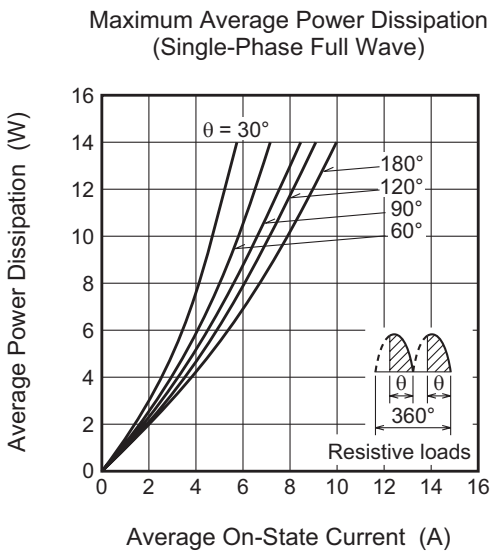
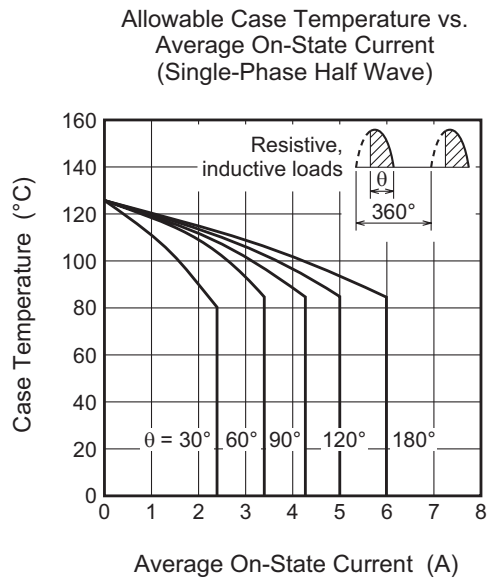
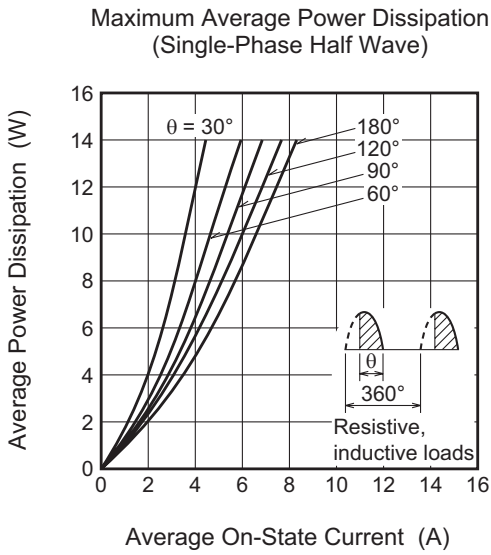


Gate Trigger Voltage vs. Junction Temperature

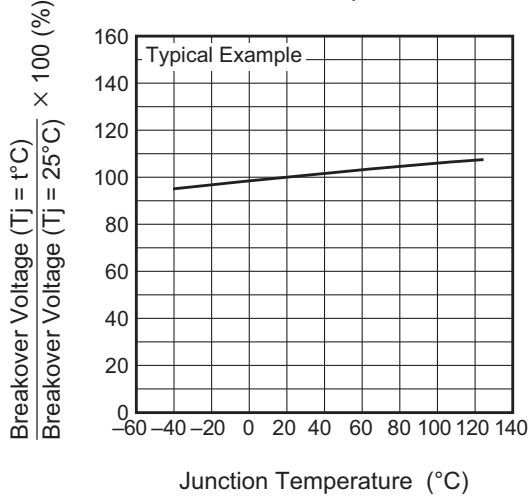


Maximum Transient Thermal Impedance Characteristics (Junction to case)

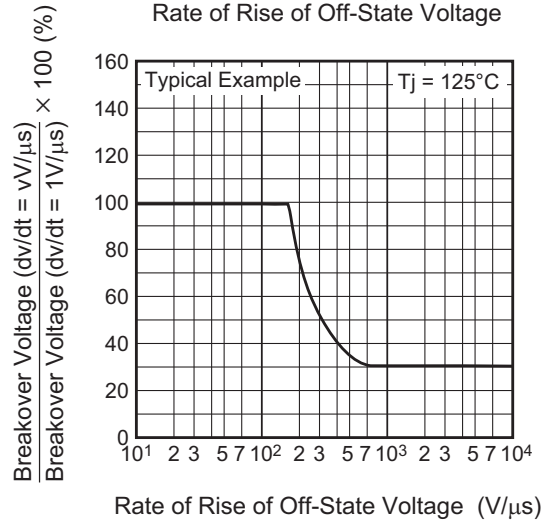




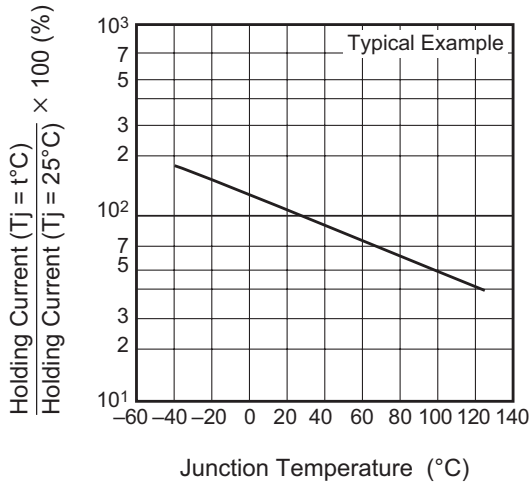
Breakover Voltage vs. Junction Temperature



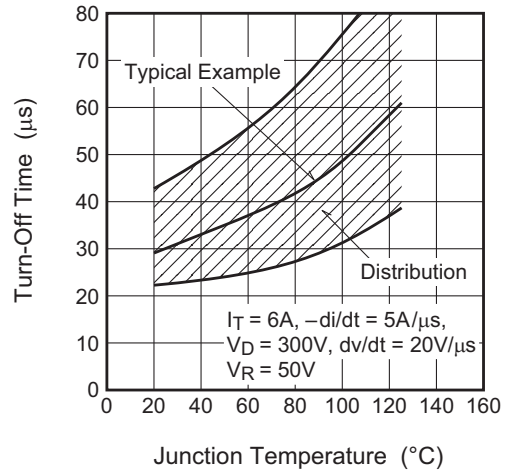
Breakover Voltage vs. Rate of Rise of Off-State Voltage



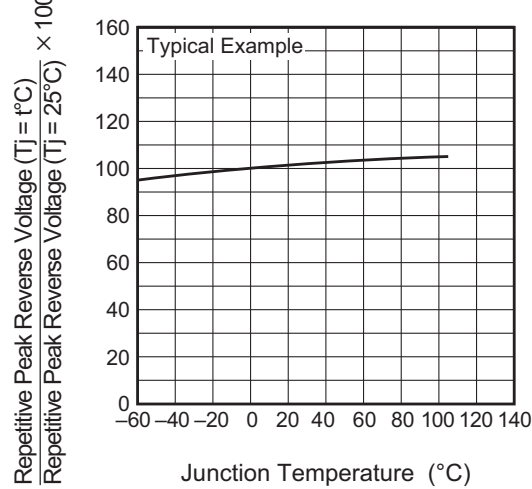
Holding Current vs. Junction Temperature



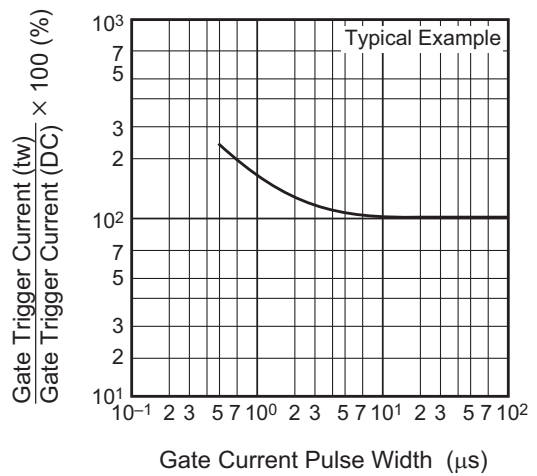
Turn-Off Time vs. Junction Temperature



Repetitive Peak Reverse Voltage vs. Junction Temperature



Gate Trigger Current vs. Gate Current Pulse Width



Package Dimensions

TO-220F

EIAJ Package Code	JEDEC Code	Mass (g) (reference value)	Lead Material
Conforms	—	2.0	Cu alloy

Note 1) The dimensional figures indicate representative values unless otherwise the tolerance is specified.

Symbol	Dimension in Millimeters		
	Min	Typ	Max
A	—	—	—
A ₁	—	—	—
A ₂	—	—	—
b	—	—	—
D	—	—	—
E	—	—	—
e	—	—	—
x	—	—	—
y	—	—	—
y ₁	—	—	—
ZD	—	—	—
ZE	—	—	—

Order Code

Lead form	Standard packing	Quantity	Standard order code	Standard order code example
Straight type	Vinyl sack	100	Type name +A	CR6PM-12A
Lead form	Plastic Magazine (Tube)	50	Type name +A – Lead forming code	CR6PM-12A-A8

Note : Please confirm the specification about the shipping in detail.

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